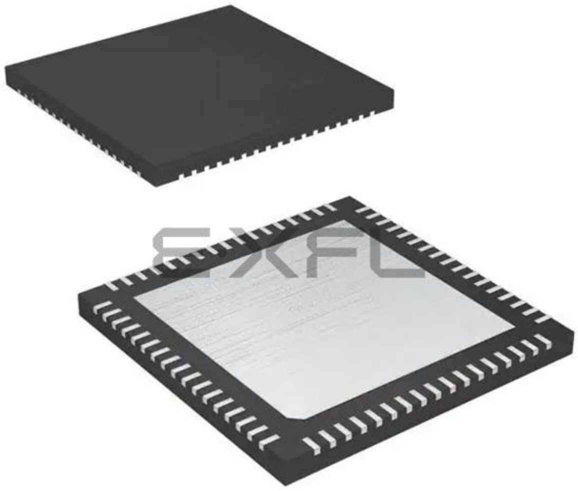

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	49
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/agl030v5-qng68i

Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO Sleep Mode*

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI / VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI / VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI / VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI / VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	µA

Note: IDD = N_{BANKS} × ICCI. Values do not include I/O static contribution, which is shown in Table 2-13 on page 2-10 through Table 2-15 on page 2-11 and Table 2-16 on page 2-11 through Table 2-18 on page 2-12 (PDC6 and PDC7).

Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO Shutdown Mode

	Core Voltage	AGL015	AGL030	Units
Typical (25°C)	1.2 V / 1.5 V	0	0	µA

Table 2-12 • Quiescent Supply Current (IDD), No IGLOO Flash*Freeze Mode[1]

	Core Voltage	AGL015	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000	Units
ICCA Current[2]										
Typical (25°C)	1.2 V	5	6	10	13	18	25	28	42	µA
	1.5 V	14	16	20	28	44	66	82	137	µA
ICCI or IJTAG Current[3]										
VCCI / VJTAG = 1.2 V (per bank) Typical (25°C)	1.2 V	1.7	1.7	1.7	1.7	1.7	1.7	1.7	1.7	µA
VCCI/VJTAG = 1.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.8	1.8	1.8	1.8	1.8	1.8	1.8	1.8	µA
VCCI/VJTAG = 1.8 V (per bank) Typical (25°C)	1.2 V / 1.5 V	1.9	1.9	1.9	1.9	1.9	1.9	1.9	1.9	µA
VCCI/VJTAG = 2.5 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.2	2.2	2.2	2.2	2.2	2.2	2.2	2.2	µA
VCCI/VJTAG = 3.3 V (per bank) Typical (25°C)	1.2 V / 1.5 V	2.5	2.5	2.5	2.5	2.5	2.5	2.5	2.5	µA

Notes:

1. *IDD = N_{BANKS} × ICCI + ICCA. JTAG counts as one bank when powered.*
2. *Includes VCC, VPUMP, and VCCPLL currents.*
3. *Values do not include I/O static contribution (PDC6 and PDC7).*

Table 2-20 • **Different Components Contributing to the Static Power Consumption in IGLOO Devices For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage**

Parameter	Definition	Device-Specific Static Power (mW)							
		AGL1000	AGL600	AGL400	AGL250	AGL125	AGL060	AGL030	AGL015
PDC1	Array static power in Active mode	See Table 2-12 on page 2-9.							
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-8.							
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.							
PDC4	Static PLL contribution	1.84							
PDC5	Bank quiescent power (V_{CCI}-dependent)	See Table 2-12 on page 2-9.							
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-10 through Table 2-15 on page 2-11.							
PDC7	I/O output pin static power (standard-dependent)	See Table 2-16 on page 2-11 through Table 2-18 on page 2-12.							

*Note: *For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power spreadsheet calculator or SmartPower tool in Libero SoC.*

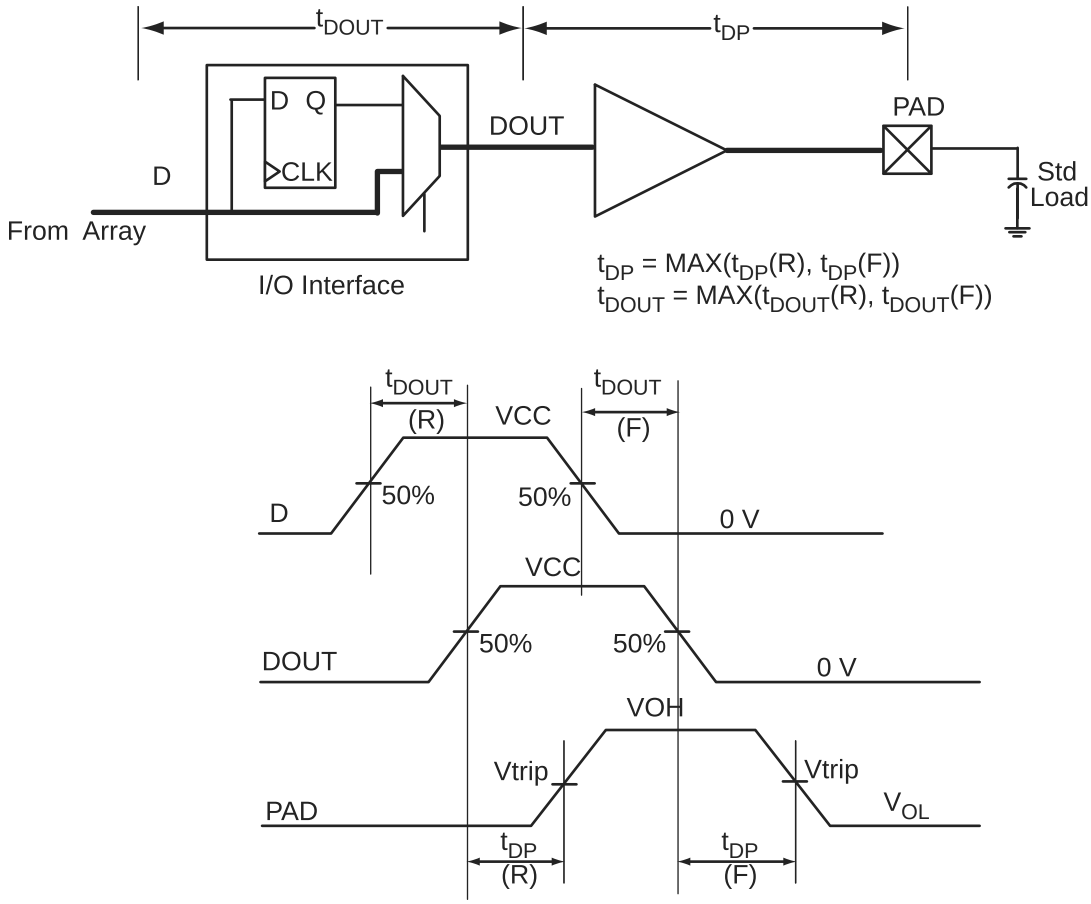

Figure 2-5 • **Output Buffer Model and Delays (example)**

Table 2-39 • **I/O Output Buffer Maximum Resistances[1]**
Applicable to Standard Plus I/O Banks

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω)[2]	$R_{PULL\text{-}UP}$ (Ω)[3]
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
1.2 V LVCMOS[4]	2 mA	158	164
1.2 V LVCMOS Wide Range[4]	100 µA	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)} = (VOLspec) / I_{OLspec}$
3. $R_{(PULL\text{-}UP\text{-}MAX)} = (VCCImax – VOHspec) / I_{OHspec}$
4. *Applicable to IGLOO V2 Devices operating at VCCI ≥ VCC*

Table 2-97 • Minimum and Maximum DC Input and Output Levels Applicable to Standard I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	2	2	9	11	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4	17	22	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

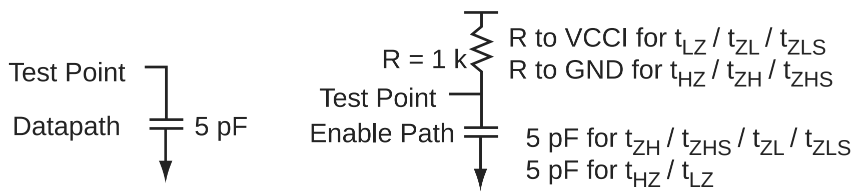

Figure 2-9 • AC Loading

Table 2-98 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.8	0.9	5

Note: **Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-99 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	6.38	0.18	1.01	0.66	6.51	5.93	2.33	1.56	10.10	9.53	ns
4 mA	Std.	0.97	5.35	0.18	1.01	0.66	5.46	5.04	2.67	2.38	9.05	8.64	ns
6 mA	Std.	0.97	4.62	0.18	1.01	0.66	4.71	4.44	2.90	2.79	8.31	8.04	ns
8 mA	Std.	0.97	4.37	0.18	1.01	0.66	4.46	4.31	2.95	2.89	8.05	7.90	ns
12 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns
16 mA	Std.	0.97	4.32	0.18	1.01	0.66	4.37	4.32	3.03	3.30	7.97	7.92	ns

Note: *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-111 **• Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks**

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**μA[4]**	**μA[4]**
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	6	6	32	39	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	8	8	66	55	10	10
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12	66	55	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-112 **• Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks**

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[3]**	**Max. mA[3]**	**μA[4]**	**μA[4]**
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Output Enable Register

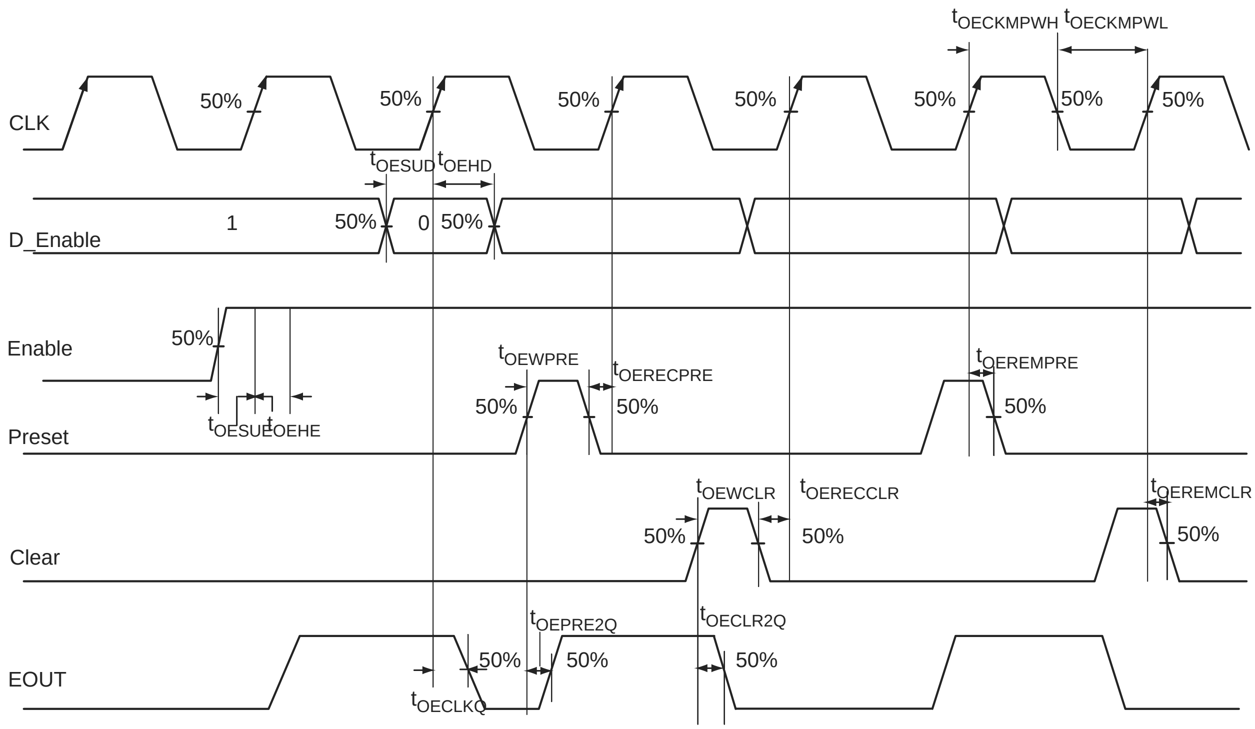

Figure 2-20 • **Output Enable Register Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-161 • **Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.75	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.51	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.73	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.13	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.13	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

DDR Module Specifications

Input DDR Module

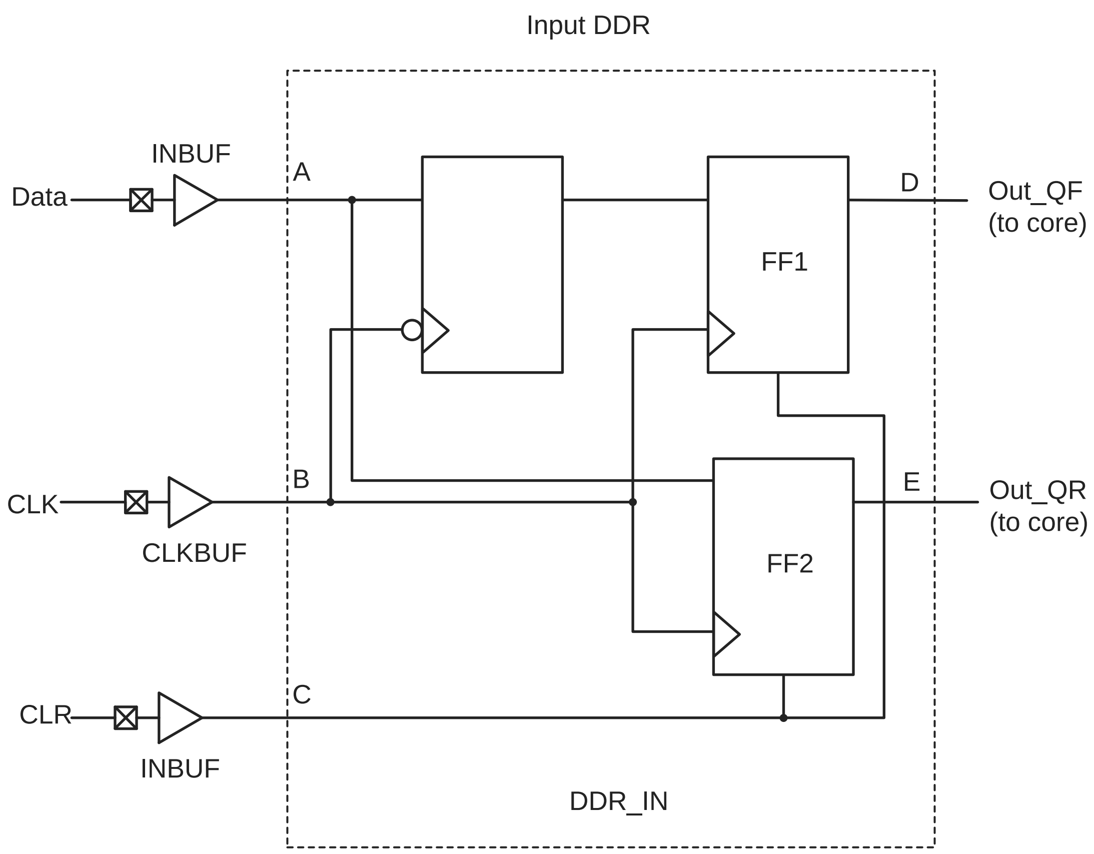

***Figure 2-21* • Input DDR Timing Model**

***Table 2-163* • Parameter Definitions**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
$t_{DDRICLKQ1}$	Clock-to-Out Out_QR	B, D
$t_{DDRICLKQ2}$	Clock-to-Out Out_QF	B, E
$t_{DDRISUD}$	Data Setup Time of DDR input	A, B
t_{DDRIHD}	Data Hold Time of DDR input	A, B
$t_{DDRICLR2Q1}$	Clear-to-Out Out_QR	C, D
$t_{DDRICLR2Q2}$	Clear-to-Out Out_QF	C, E
$t_{DDRIREMCLR}$	Clear Removal	C, B
$t_{DDRIRECCLR}$	Clear Recovery	C, B

***Table 2-190* • IGLOO CCC/PLL Specification**
For IGLOO V2 Devices, 1.2 V DC Core Supply Voltage

Parameter	Min.	Typ.	Max.	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		160	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		160	MHz
Delay Increments in Programmable Delay Blocks [1, 2]		580[3]		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Serial Clock (SCLK) for Dynamic PLL[4,5]			60	ns
Input Cycle-to-Cycle Jitter (peak magnitude)			0.25	ns
Acquisition Time				
LockControl = 0			300	µs
LockControl = 1			6.0	ms
Tracking Jitter[6]				
LockControl = 0			4	ns
LockControl = 1			3	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1[1,2]	2.3		20.86	ns
Delay Range in Block: Programmable Delay 2[1,2]	0.863		20.86	ns
Delay Range in Block: Fixed Delay [1, 2, 5]		5.7		ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Maximum Peak-to-Peak Jitter Data[7,8]			
	SSO ≥ 4[9]	SSO ≥ 8[9]	SSO ≥ 16[9]	
0.75 MHz to 50 MHz	1.20%	2.00%	3.00%	
50 MHz to 160 MHz	5.00%	7.00%	15.00%	

Notes:

1. *This delay is a function of voltage and temperature. See Table 2-6 on page 2-7 and Table 2-7 on page 2-7 for deratings.*
2. *T_J = 25°C, V_{CC} = 1.2 V*
3. *When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.*
4. *Maximum value obtained for a Std. speed grade device in Worst-Case Commercial Conditions. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
5. *The AGL030 device does not support a PLL.*
6. *Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.*
7. *VCO output jitter is calculated as a percentage of the VCO frequency. The jitter (in ps) can be calculated by multiplying the VCO period by the per cent jitter. The VCO jitter (in ps) applies to CCC_OUT regardless of the output divider settings. For example, if the jitter on VCO is 300 ps, the jitter on CCC_OUT is also 300 ps, regardless of the output divider settings.*
8. *Measurements done with LVTTL 3.3 V, 8 mA I/O drive strength, and high slew Rate. VCC/VCCPLL = 1.14 V, VQ/PQ/TQ type of packages, 20 pF load.*
9. *SSO are outputs that are synchronous to a single clock domain and have clock-to-out times that are within ±200 ps of each other. Switching I/Os are placed outside of the PLL bank. Refer to the "Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout" section in the IGLOO FPGA Fabric User Guide.*
10. *For definitions of Type 1 and Type 2, refer to the PLL Block Diagram in the "Clock Conditioning Circuits in IGLOO and ProASIC3 Devices" chapter of the IGLOO FPGA Fabric User Guide.*

Embedded SRAM and FIFO Characteristics

SRAM

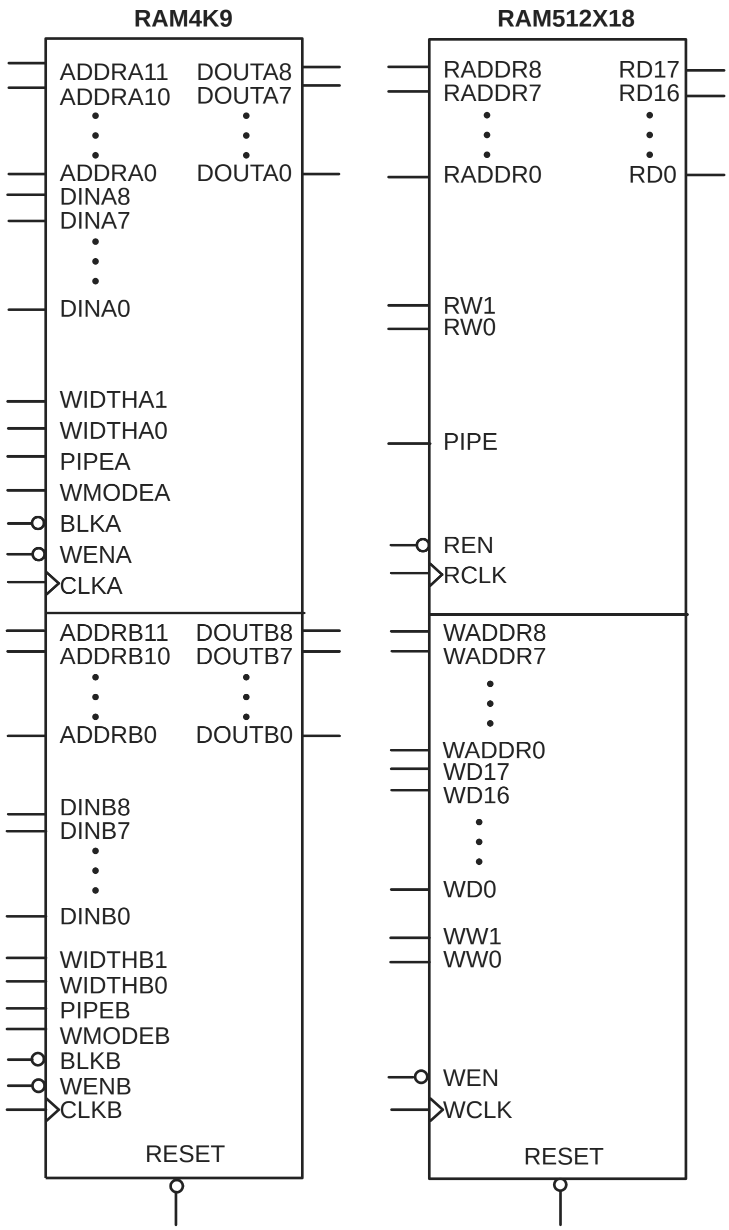

Figure 2-31 • **RAM Models**

Timing Waveforms

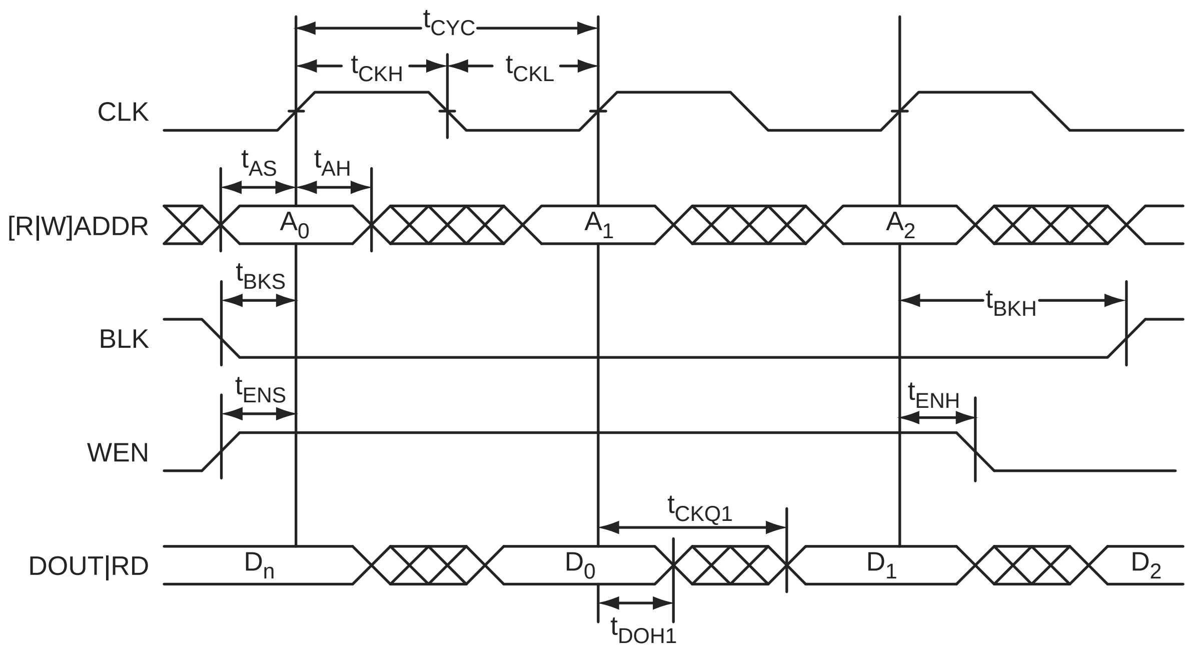

Figure 2-32 • **RAM Read for Pass-Through Output. Applicable to Both RAM4K9 and RAM512x18.**

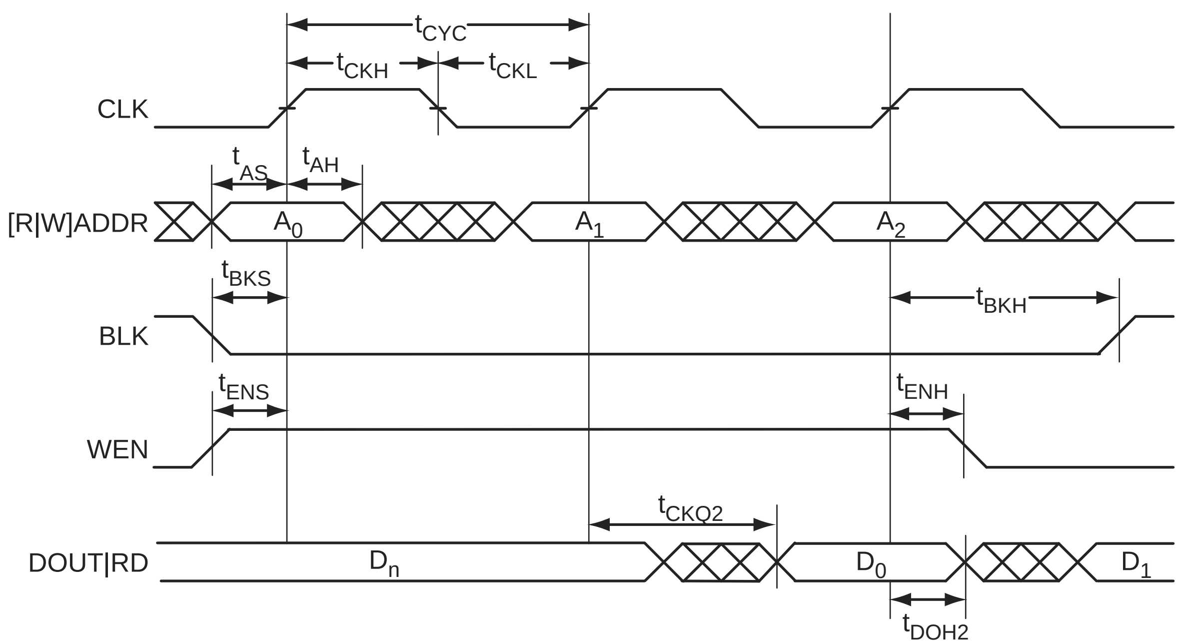

Figure 2-33 • **RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.**

***Table 2-192* • RAM512X18**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.73	ns
t_{ENH}	REN, WEN hold time	0.08	ns
t_{DS}	Input data (WD) setup time	0.71	ns
t_{DH}	Input data (WD) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on RD (output retained)	4.21	ns
t_{CKQ2}	Clock High to new data valid on RD (pipelined)	1.71	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address - Applicable to Opening Edge	0.35	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address - Applicable to Opening Edge	0.42	ns
t_{RSTBQ}	RESET Low to data out Low on RD (flow-through)	2.06	ns
	RESET Low to data out Low on RD (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs*.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

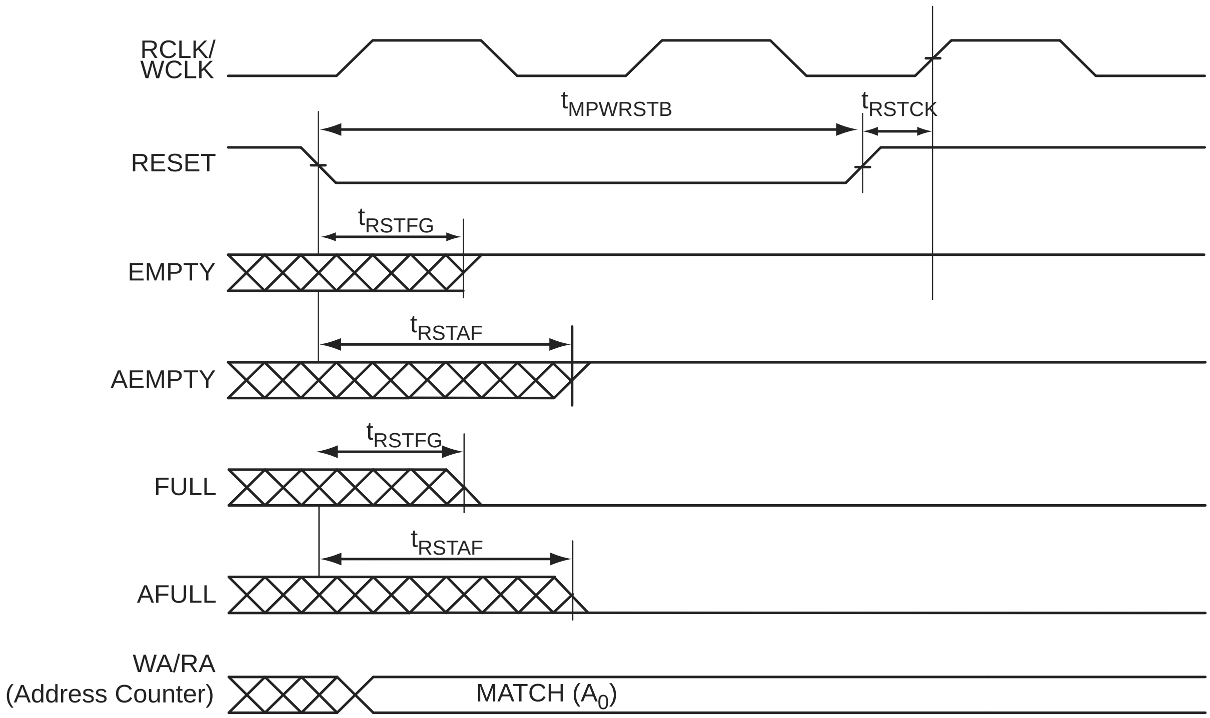

Figure 2-40 • **FIFO Reset**

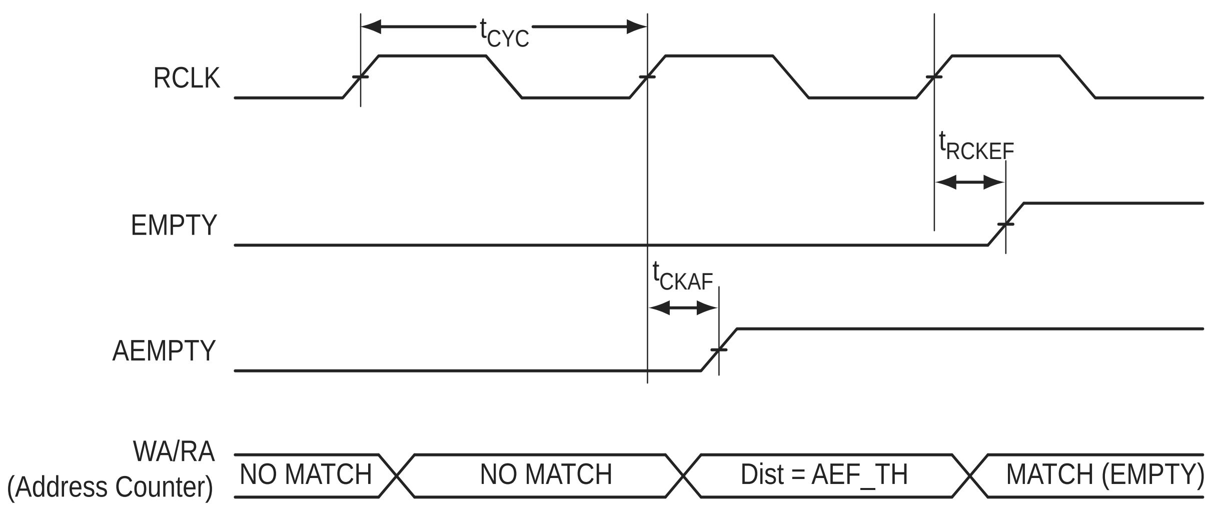

Figure 2-41 • **FIFO EMPTY Flag and AEMPTY Flag Assertion**

CS196	
Pin Number	**AGL400 Function**
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO14RSB0
A6	IO18RSB0
A7	IO26RSB0
A8	IO29RSB0
A9	IO36RSB0
A10	GBC0/IO54RSB0
A11	GBB0/IO56RSB0
A12	GBB1/IO57RSB0
A13	GBA1/IO59RSB0
A14	GND
B1	VCCIB3
B2	VMV0
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO17RSB0
B7	IO25RSB0
B8	IO34RSB0
B9	IO39RSB0
B10	GND
B11	GBC1/IO55RSB0
B12	GBA0/IO58RSB0
B13	GBA2/IO60PPB1
B14	GBB2/IO61PDB1
C1	GAC2/IO153UDB3
C2	GAB2/IO154UDB3
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO15RSB0
C7	VCCIB0

CS196	
Pin Number	**AGL400 Function**
C8	IO31RSB0
C9	IO44RSB0
C10	IO49RSB0
C11	VCCIB0
C12	IO60NPB1
C13	GNDQ
C14	IO61NDB1
D1	IO153VDB3
D2	IO154VDB3
D3	GAA2/IO155UDB3
D4	IO150PPB3
D5	IO11RSB0
D6	IO20RSB0
D7	IO23RSB0
D8	IO28RSB0
D9	IO41RSB0
D10	IO47RSB0
D11	IO63PPB1
D12	VMV1
D13	IO62NDB1
D14	GBC2/IO62PDB1
E1	IO149PDB3
E2	GND
E3	IO155VDB3
E4	VCCIB3
E5	IO151USB3
E6	IO09RSB0
E7	IO12RSB0
E8	IO32RSB0
E9	IO46RSB0
E10	IO51RSB0
E11	VCCIB1
E12	IO63NPB1
E13	GND
E14	IO64PDB1
F1	IO149NDB3

CS196	
Pin Number	**AGL400 Function**
F2	IO144NPB3
F3	IO148PDB3
F4	IO148NDB3
F5	IO150NPB3
F6	IO07RSB0
F7	VCC
F8	VCC
F9	IO43RSB0
F10	IO73PDB1
F11	IO73NDB1
F12	IO66NDB1
F13	IO66PDB1
F14	IO64NDB1
G1	GFB1/IO146PDB3
G2	GFA0/IO145NDB3
G3	GFA2/IO144PPB3
G4	VCOMPLF
G5	GFC0/IO147NDB3
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO67NDB1
G11	GCB1/IO68PDB1
G12	GCA0/IO69NDB1
G13	IO72NDB1
G14	GCC2/IO72PDB1
H1	GFB0/IO146NDB3
H2	GFA1/IO145PDB3
H3	VCCPLF
H4	GFB2/IO143PPB3
H5	GFC1/IO147PDB3
H6	VCC
H7	GND
H8	GND
H9	VCC

FG144	
Pin Number	AGL1000 Function
A1	GNDQ
A2	VMV0
A3	GAB0/IO02RSB0
A4	GAB1/IO03RSB0
A5	IO10RSB0
A6	GND
A7	IO44RSB0
A8	VCC
A9	IO69RSB0
A10	GBA0/IO76RSB0
A11	GBA1/IO77RSB0
A12	GNDQ
B1	GAB2/IO224PDB3
B2	GND
B3	GAA0/IO00RSB0
B4	GAA1/IO01RSB0
B5	IO13RSB0
B6	IO26RSB0
B7	IO35RSB0
B8	IO60RSB0
B9	GBB0/IO74RSB0
B10	GBB1/IO75RSB0
B11	GND
B12	VMV1
C1	IO224NDB3
C2	GFA2/IO206PPB3
C3	GAC2/IO223PDB3
C4	VCC
C5	IO16RSB0
C6	IO29RSB0
C7	IO32RSB0
C8	IO63RSB0
C9	IO66RSB0
C10	GBA2/IO78PDB1
C11	IO78NDB1
C12	GBC2/IO80PPB1

FG144	
Pin Number	AGL1000 Function
D1	IO213PDB3
D2	IO213NDB3
D3	IO223NDB3
D4	GAA2/IO225PPB3
D5	GAC0/IO04RSB0
D6	GAC1/IO05RSB0
D7	GBC0/IO72RSB0
D8	GBC1/IO73RSB0
D9	GBB2/IO79PDB1
D10	IO79NDB1
D11	IO80NPB1
D12	GCB1/IO92PPB1
E1	VCC
E2	GFC0/IO209NDB3
E3	GFC1/IO209PDB3
E4	VCCIB3
E5	IO225NPB3
E6	VCCIB0
E7	VCCIB0
E8	GCC1/IO91PDB1
E9	VCCIB1
E10	VCC
E11	GCA0/IO93NDB1
E12	IO94NDB1
F1	GFB0/IO208NPB3
F2	VCOMPLF
F3	GFB1/IO208PPB3
F4	IO206NPB3
F5	GND
F6	GND
F7	GND
F8	GCC0/IO91NDB1
F9	GCB0/IO92NPB1
F10	GND
F11	GCA1/IO93PDB1
F12	GCA2/IO94PDB1

FG144	
Pin Number	AGL1000 Function
G1	GFA1/IO207PPB3
G2	GND
G3	VCCPLF
G4	GFA0/IO207NPB3
G5	GND
G6	GND
G7	GND
G8	GDC1/IO111PPB1
G9	IO96NDB1
G10	GCC2/IO96PDB1
G11	IO95NDB1
G12	GCB2/IO95PDB1
H1	VCC
H2	GFB2/IO205PDB3
H3	GFC2/IO204PSB3
H4	GEC1/IO190PDB3
H5	VCC
H6	IO105PDB1
H7	IO105NDB1
H8	GDB2/IO115RSB2
H9	GDC0/IO111NPB1
H10	VCCIB1
H11	IO101PSB1
H12	VCC
J1	GEB1/IO189PDB3
J2	IO205NDB3
J3	VCCIB3
J4	GEC0/IO190NDB3
J5	IO160RSB2
J6	IO157RSB2
J7	VCC
J8	TCK
J9	GDA2/IO114RSB2
J10	TDO
J11	GDA1/IO113PDB1
J12	GDB1/IO112PDB1

FG256	
Pin Number	AGL600 Function
R5	IO132RSB2
R6	IO127RSB2
R7	IO121RSB2
R8	IO114RSB2
R9	IO109RSB2
R10	IO105RSB2
R11	IO98RSB2
R12	IO96RSB2
R13	GDB2/IO90RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO137RSB2
T3	FF/GEB2/IO142RSB2
T4	IO134RSB2
T5	IO125RSB2
T6	IO123RSB2
T7	IO118RSB2
T8	IO115RSB2
T9	IO111RSB2
T10	IO106RSB2
T11	IO102RSB2
T12	GDC2/IO91RSB2
T13	IO93RSB2
T14	GDA2/IO89RSB2
T15	TMS
T16	GND

FG484	
Pin Number	AGL400 Function
E13	IO38RSB0
E14	IO42RSB0
E15	GBC1/IO55RSB0
E16	GBB0/IO56RSB0
E17	IO44RSB0
E18	GBA2/IO60PDB1
E19	IO60NDB1
E20	GND
E21	NC
E22	NC
F1	NC
F2	NC
F3	NC
F4	IO154VDB3
F5	IO155VDB3
F6	IO11RSB0
F7	IO07RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO20RSB0
F11	IO24RSB0
F12	IO33RSB0
F13	IO39RSB0
F14	IO45RSB0
F15	GBC0/IO54RSB0
F16	IO48RSB0
F17	VMV0
F18	IO61NPB1
F19	IO63PDB1
F20	NC
F21	NC
F22	NC
G1	NC
G2	NC
G3	NC
G4	IO151VDB3

FG484	
Pin Number	AGL400 Function
U1	NC
U2	NC
U3	NC
U4	GEB1/IO136PDB3
U5	GEB0/IO136NDB3
U6	VMV2
U7	IO129RSB2
U8	IO128RSB2
U9	IO122RSB2
U10	IO115RSB2
U11	IO110RSB2
U12	IO98RSB2
U13	IO95RSB2
U14	IO88RSB2
U15	IO84RSB2
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO79VDB1
U20	NC
U21	NC
U22	NC
V1	NC
V2	NC
V3	GND
V4	GEA1/IO135PDB3
V5	GEA0/IO135NDB3
V6	IO127RSB2
V7	GEC2/IO132RSB2
V8	IO123RSB2
V9	IO118RSB2
V10	IO112RSB2
V11	IO106RSB2
V12	IO100RSB2
V13	IO96RSB2
V14	IO89RSB2

FG484	
Pin Number	**AGL1000 Function**
E13	IO51RSB0
E14	IO57RSB0
E15	GBC1/IO73RSB0
E16	GBB0/IO74RSB0
E17	IO71RSB0
E18	GBA2/IO78PDB1
E19	IO81PDB1
E20	GND
E21	NC
E22	IO84PDB1
F1	NC
F2	IO215PDB3
F3	IO215NDB3
F4	IO224NDB3
F5	IO225NDB3
F6	VMV3
F7	IO11RSB0
F8	GAC0/IO04RSB0
F9	GAC1/IO05RSB0
F10	IO25RSB0
F11	IO36RSB0
F12	IO42RSB0
F13	IO49RSB0
F14	IO56RSB0
F15	GBC0/IO72RSB0
F16	IO62RSB0
F17	VMV0
F18	IO78NDB1
F19	IO81NDB1
F20	IO82PPB1
F21	NC
F22	IO84NDB1
G1	IO214NDB3
G2	IO214PDB3
G3	NC
G4	IO222NDB3

Revision	Changes	Page
Revision 19 (continued)	The following sentence was removed from the "Advanced Architecture" section: "In addition, extensive on-chip programming circuitry allows for rapid, single-voltage (3.3 V) programming of IGLOO devices via an IEEE 1532 JTAG interface" (SAR 28756).	1-3
	The "Specifying I/O States During Programming" section is new (SAR 21281).	1-8
	Values for VCCPLL at 1.2 V –1.5 V DC core supply voltage were revised in Table 2-2 • Recommended Operating Conditions 1 (SAR 22356). The value for VPUMP operation was changed from "0 to 3.45 V" to "0 to 3.6 V" (SAR 25220). The value for VCCPLL 1.5 V DC core supply voltage was changed from "1.4 to 1.6 V" to "1.425 to 1.575 V" (SAR 26551). The notes in the table were renumbered in order of their appearance in the table (SAR 21869).	2-2
	The temperature used in EQ 2 was revised from 110°C to 100°C for consistency with the limits given in Table 2-2 • Recommended Operating Conditions 1. The resulting maximum power allowed is thus 1.28 W. Formerly it was 1.71 W (SAR 26259).	2-6
	Values for CS196, CS281, and QN132 packages were added to Table 2-5 • Package Thermal Resistivities (SARs 26228, 32301).	2-6
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.425 V) and Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays (normalized to TJ = 70°C, VCC = 1.14 V) were updated to remove the column for –20°C and shift the data over to correct columns (SAR 23041).	2-7
	The tables in the "Quiescent Supply Current" section were updated with revised notes on IDD (SAR 24112). Table 2-8 • Power Supply State per Mode is new.	2-7
	The formulas in the table notes for Table 2-41 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 21348).	2-37
	The row for 110°C was removed from Table 2-45 • Duration of Short Circuit Event before Failure. The example in the associated paragraph was changed from 110°C to 100°C. Table 2-46 • I/O Input Rise Time, Fall Time, and Related I/O Reliability1 was revised to change 110° to 100°C. (SAR 26259).	2-40
	The notes regarding drive strength in the "Summary of I/O Timing Characteristics – Default I/O Software Settings" section, "3.3 V LVCMOS Wide Range" section and "1.2 V LVCMOS Wide Range" section tables were revised for clarification. They now state that the minimum drive strength for the default software configuration when run in wide range is ±100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-28, 2-47, 2-77
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-56
	The values for $F_{DDRIMAX}$ and F_{DDOMAX} were updated in the tables in the "Input DDR Module" section and "Output DDR Module" section (SAR 23919).	2-94, 2-97
	The following notes were removed from Table 2-147 • Minimum and Maximum DC Input and Output Levels (SAR 29428): ±5% Differential input voltage = ±350 mV	2-81
	Table 2-189 • IGLOO CCC/PLL Specification and Table 2-190 • IGLOO CCC/PLL Specification were updated. A note was added to both tables indicating that when the CCC/PLL core is generated by Mircosemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-115